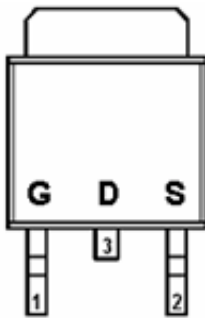


DESCRIPTION

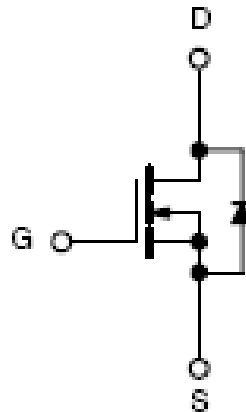
STN18T20 is the N-Channel logic enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as power management and other battery powered circuits where high-side switching.

**PIN CONFIGURATION
TO-252**

FEATURE

- 200V/12A, $R_{DS(ON)} = 170m\Omega$ (Typ.) @ $V_{GS} = 10V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TO-252 package design

PART MARKING


Y: Year Code
A: Date Code
Q: Process Code





STN18T20 

N Channel Enhancement Mode MOSFET

18.0A

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	VDSS	200	V
Gate-Source Voltage	VGSS	±30	V
Continuous Drain Current (TJ=150°C)	ID	TA=25°C 18	A
		TA=100°C 11.4	
Pulsed Drain Current	IDM	36	A
Avalanche Current	IAS	17	mJ
Power Dissipation	TA=25°C PD	112	W
Operation Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-55/150	°C
Thermal Resistance-Junction to Ambient	RθJA	80	°C/W



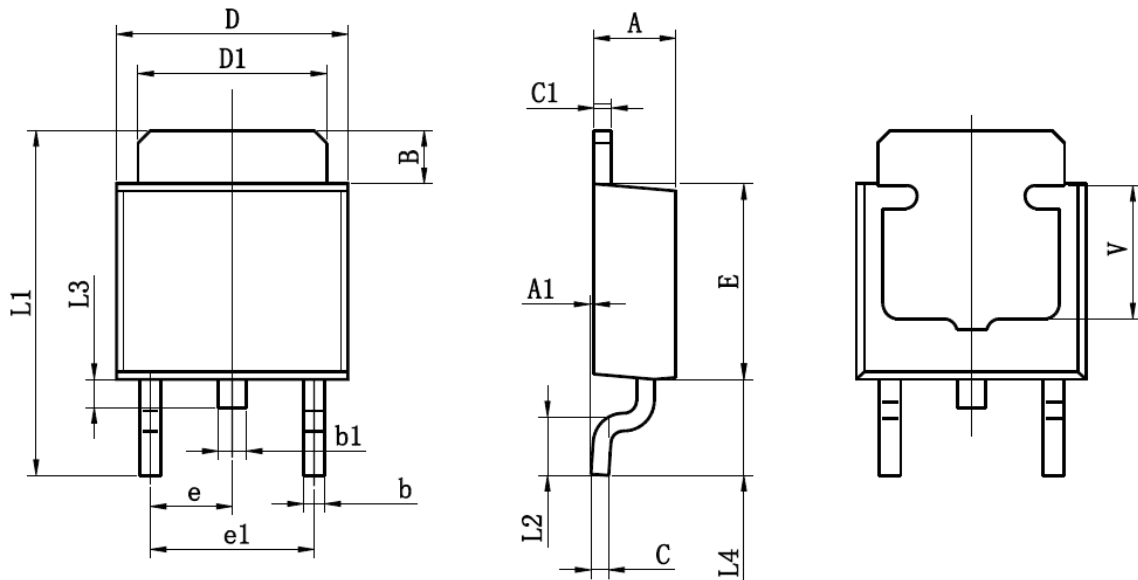
STN18T20 

N Channel Enhancement Mode MOSFET

18.0A

ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	200			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2		5	V
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 30V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=160V, V_{GS}=0V$			2	μA
On-State Drain Current	$I_{D(on)}$	$V_{DS}\geq 5V, V_{GS}=10V$	18			A
Drain-source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=12A$		170	220	m Ω
Forward Transconductance	g_{fs}	$V_{DS}=15V, I_D=20A$		8.5		S
Diode Forward Voltage	V_{SD}	$I_S=1A, V_{GS}=0V$			1	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=160V, V_{GS}=10V$ $I_D=12 A$		17.6	25	nC
Gate-Source Charge	Q_{gs}			7.6	11	
Gate-Drain Charge	Q_{gd}			3.7	5.2	
Input Capacitance	C_{iss}	$V_{DS}=25, V_{GS}=0V$ $f=1MHz$		1000	1400	pF
Output Capacitance	C_{oss}			110	155	
Reverse Transfer Capacitance	C_{rss}			2.4	3.5	
Turn-On Time	$t_{d(on)}$	$V_{DS}=100, R_G=3.3$ $V_{GEN}=10V, I_D=12 A$ $R_G=1.0\Omega$		9.4	19	nS
	t_r			23	41	
Turn-Off Time	$t_{d(off)}$			18.4	37	
	t_f			15.6	21.8	

PACKAGE OUTLINE TO-252


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300TYP		0.091TYP	
e1	4.500	4.700	0.177	0.185
L1	9.500	9.900	0.374	0.390
L2	1.400	1.780	0.055	0.070
L3	0.650	0.950	0.026	0.037
L4	2.550	2.900	0.100	0.114
V	3.80REF		0.150REF	